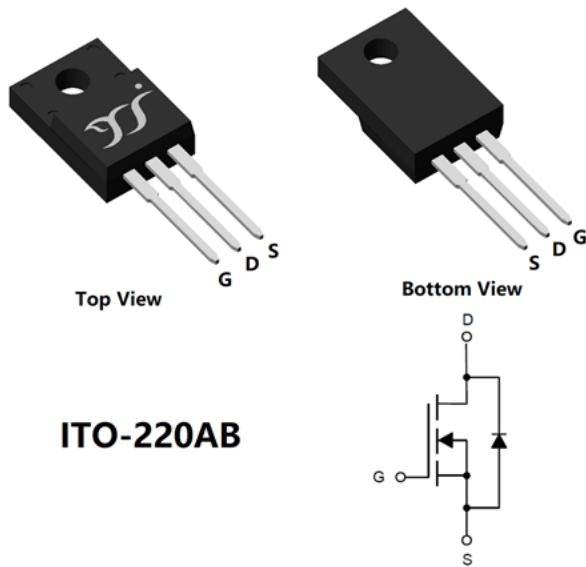


N-Channel Enhancement Mode Field Effect Transistor



ITO-220AB

Product Summary

- V_{DS} 650V
- I_D 5A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $<900m\Omega$
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Super Junction High Voltage MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Switching Mode Power Supplies (SMPS)
- PWM Motor Controls
- LED Lighting
- Adapter

Limiting Values

Parameter	Conditions	Symbol	Min	Max	Unit
Drain-source Voltage		V_{DS}	-	650	V
Gate-source Voltage		V_{GS}	-30	30	
Continuous Drain Current (Note 1,2)	Steady-State	I_D	-	0.88	A
			-	0.55	
Continuous Drain Current (Note 1,3)	Steady-State		-	5	
			-	3.1	
Pulsed Drain Current	$T_C=25^{\circ}C, t_p \leq 10\mu s$	I_{DM}	-	9.5	
Maximum Body-Diode Continuous Current	$T_C=25^{\circ}C$	I_S		5	mJ
Maximum Body-Diode Pulsed Current	$T_C=25^{\circ}C, t_p \leq 10\mu s$	I_{SM}	-	9.5	
Avalanche Energy (non-repetitive)	$T_J=25^{\circ}C, V_G=10V, R_G=25\Omega, L=30mH, I_{AS}=1.1A$	EAS	-	18.1	
Total Power Dissipation (Note 1,2)	Steady-State	P_D	-	1.71	W
			-	0.68	
Total Power Dissipation (Note 1,3)	Steady-State		-	30.4	
			-	12.1	
MOSFET dv/dt Ruggedness	$V_{DS}=0 \dots 325V, I_D \leq 3.8A, R_G=0\Omega$	dv/dt	-	99	V/ns
Reverse Diode dv/dt	$V_{DS}=0 \dots 325V, I_D \leq 3.8A, di/dt=100A/us$	dv/dt	-	47	
Maximum Diode Commutation Speed	$V_{DS}=0 \dots 325V, I_D \leq 3.8A, R_G=0\Omega$	dif/dt	-	1800	A/us
Junction and Storage Temperature Range		T_J, T_{STG}	-55	150	$^{\circ}C$

Thermal Resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	-	73	$^{\circ}C/W$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	4.1	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJF1K0D65CHJ	B1	F1K0D65CHJ	50	/	5000	Tube



YJF1K0D65CHJ

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA, T _j =25°C	650	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V, T _j =25°C	-	-	1	μA
		V _{DS} =650V, V _{GS} =0V, T _j =150°C	-	-	100	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V, T _j =25°C	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA, T _j =25°C	2.2	3	3.8	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =1A, T _j =25°C	-	780	900	mΩ
		V _{GS} =10V, I _D =1A, T _j =150°C	-	1895	2185	
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0V, T _j =25°C	-	0.84	1.2	V
Gate Resistance	R _G	f=1MHz, T _j =25°C	-	4	-	Ω
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =325V, V _{GS} =0V, f=1MHz, T _j =25°C	-	252	-	pF
Output Capacitance	C _{oss}		-	8.2	-	
Reverse Transfer Capacitance	C _{rss}		-	1.1	-	
Effective Output capacitance, Energy Related	C _{o(er)}	V _{DS} =0...325V, V _{GS} =0V, f=1MHz, T _j =25°C	-	13.7	-	
Effective Output Capacitance, Time Related	C _{o(tr)}		-	70.7	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =325V, I _D =3.8A, T _j =25°C	-	7.2	-	nC
Gate-Source Charge	Q _{gs}		-	0.9	-	
Gate-Drain Charge	Q _{gd}		-	3	-	
Reverse Recovery Charge	Q _{rr}	I _F =3.8A, di/dt=100A/μs, V _{GS} =0V, V _R =325V, T _j =25°C	-	817	-	nC
Reverse Recovery Time	t _{rr}		-	140	-	ns
Peak Reverse Recovery Current	I _{rrm}		-	10	-	A
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DS} =325V, I _D =3.8A, R _{GEN} =3Ω, T _j =25°C	-	2	-	ns
Turn-on Rise Time	t _r		-	3.4	-	
Turn-off Delay Time	t _{D(off)}		-	6.9	-	
Turn-off Fall Time	t _f		-	5.4	-	

Note:

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of $R_{\theta JA}$ is measured in the still air environment with $T_A=25^\circ C$. The maximum allowed junction temperature of $150^\circ C$.
3. Thermal resistance from junction to soldering point (on the exposed drain pad).



■ Typical Electrical and Thermal Characteristics Diagrams

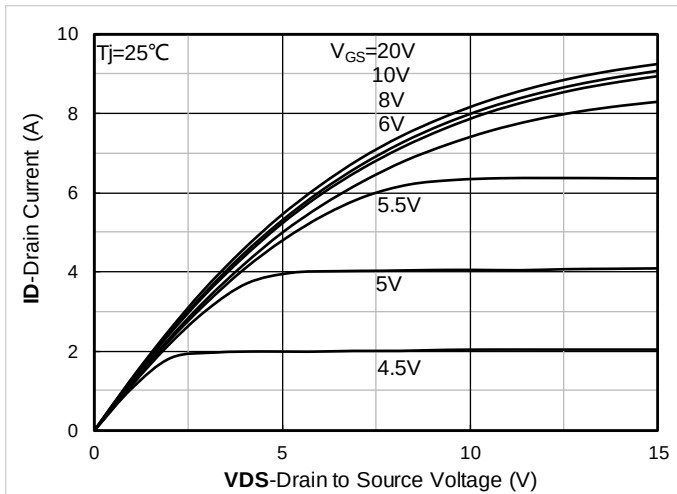


Figure 1. Output Characteristics; typical values

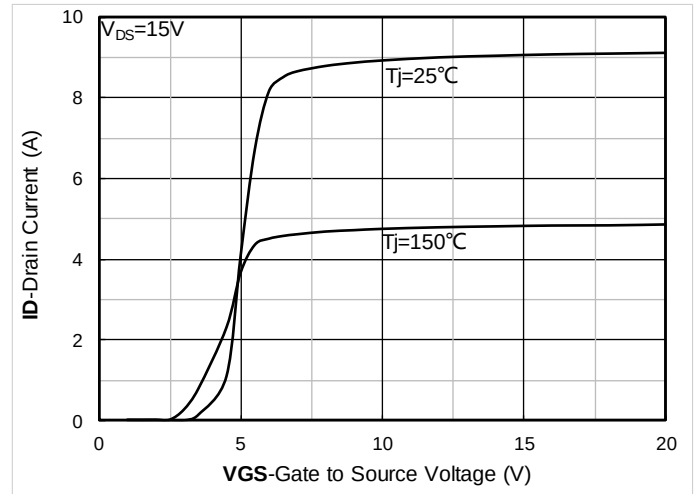


Figure 2. Transfer Characteristics; typical values

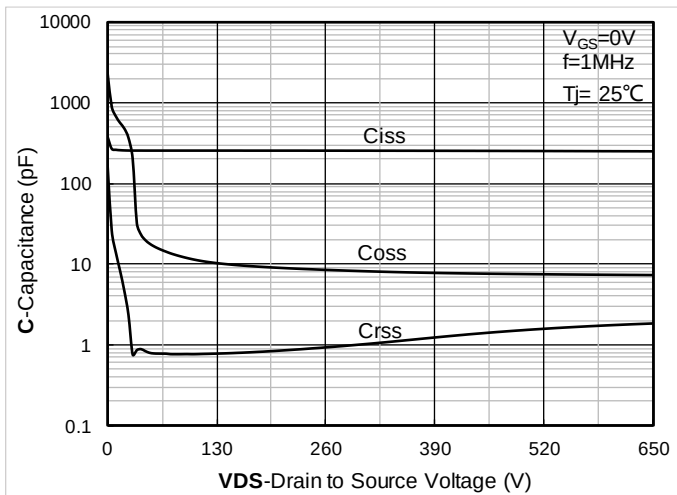


Figure 3. Capacitance Characteristics; typical values

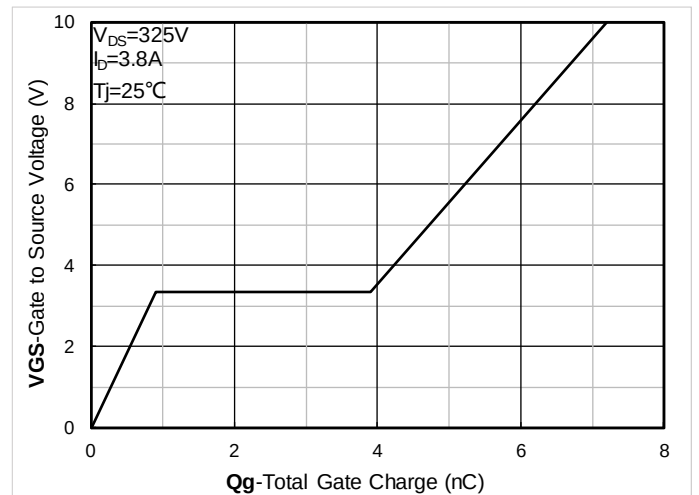


Figure 4. Gate Charge; typical values

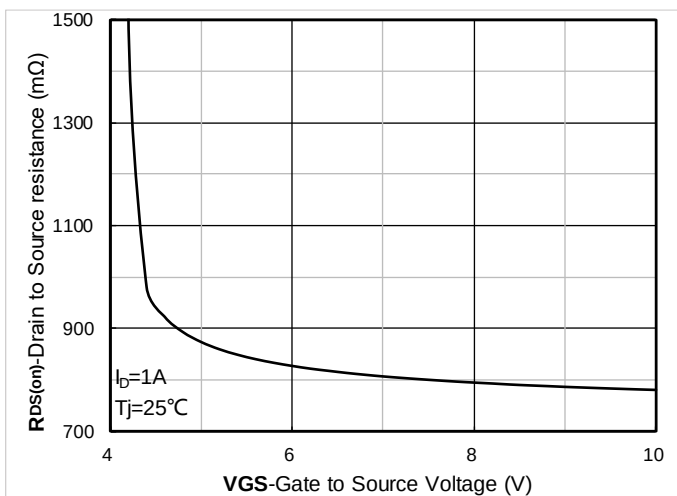


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

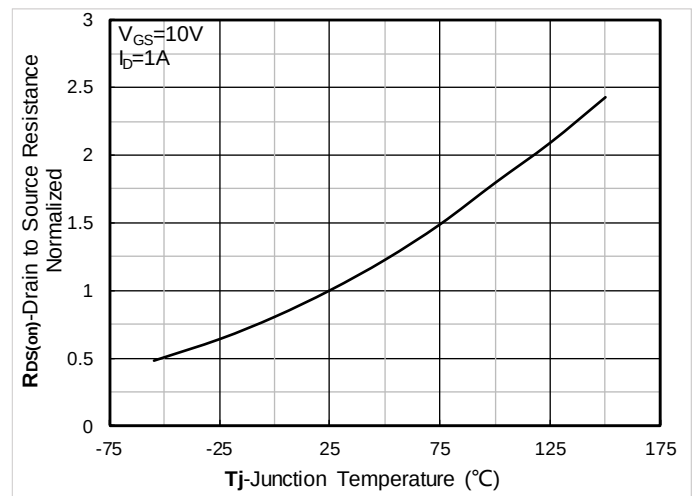


Figure 6. Normalized On-Resistance

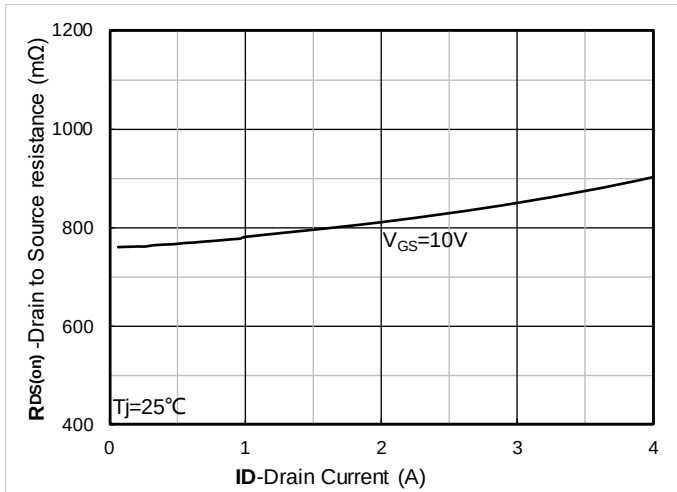


Figure 7. RDS(on) vs. Drain Current; typical values

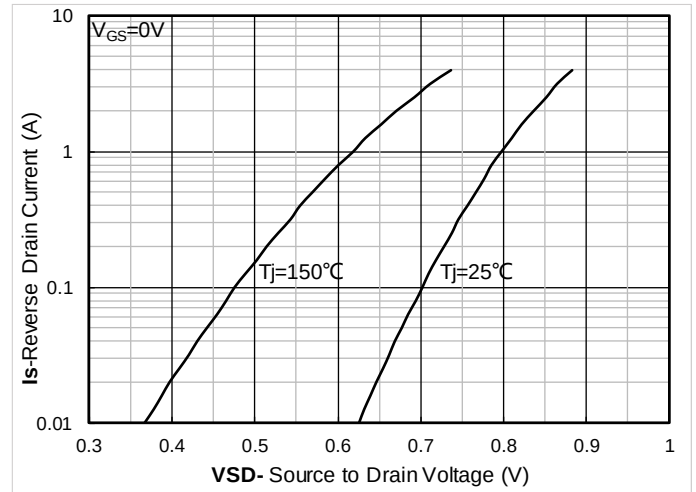


Figure 8. Forward characteristics of reverse diode; typical values

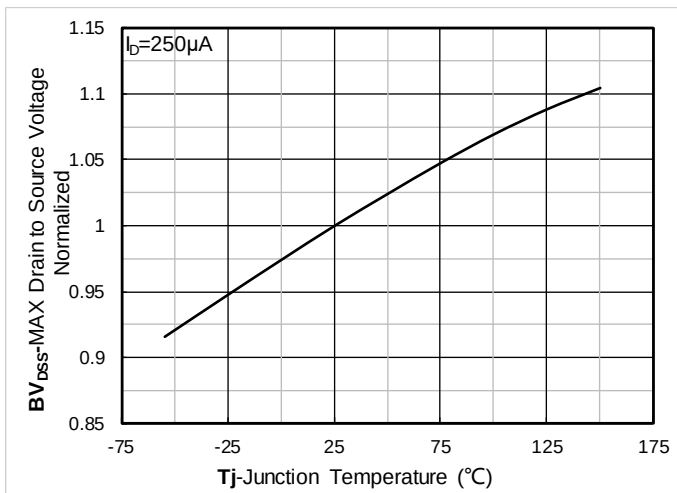


Figure 9. Normalized breakdown voltage

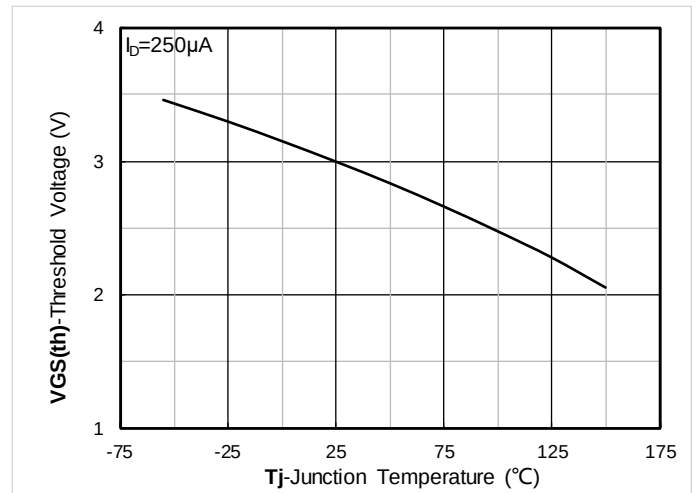


Figure 10. Gate Threshold voltage; typical values

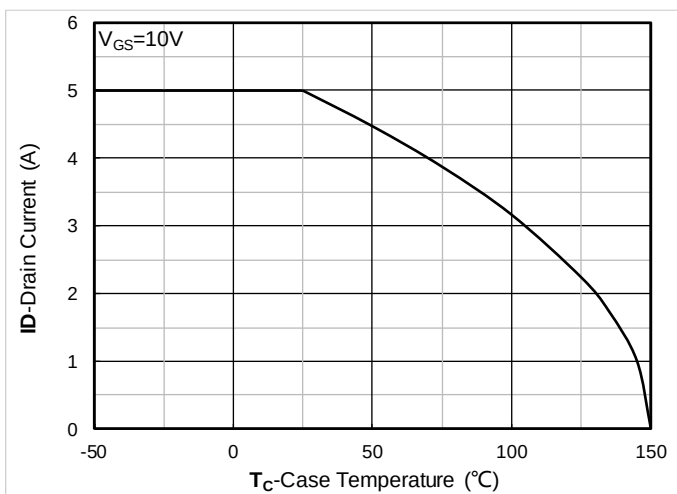


Figure 11. Current dissipation

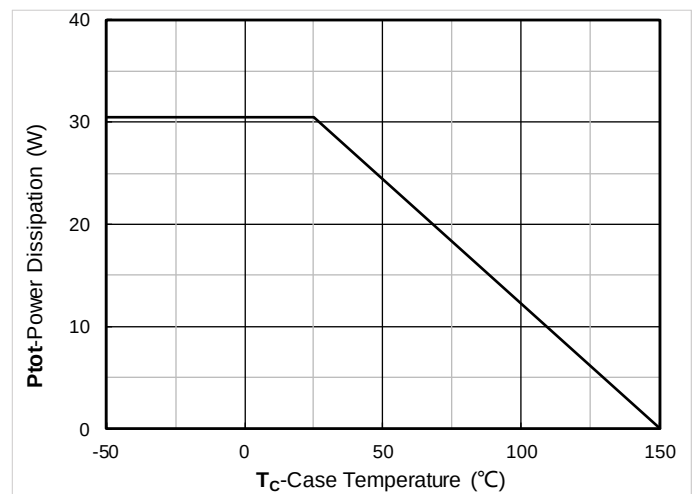


Figure 12. Power dissipation

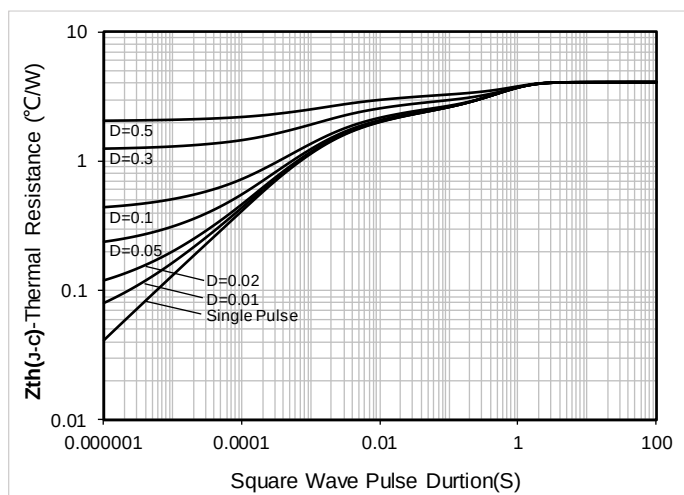


Figure 13. Maximum Transient Thermal Impedance

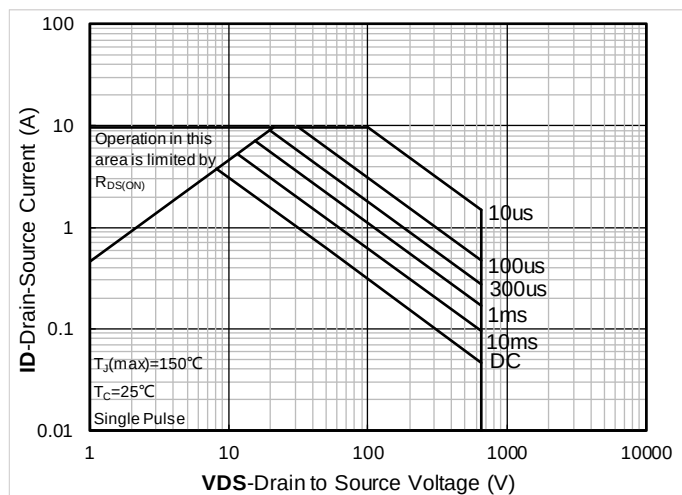


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

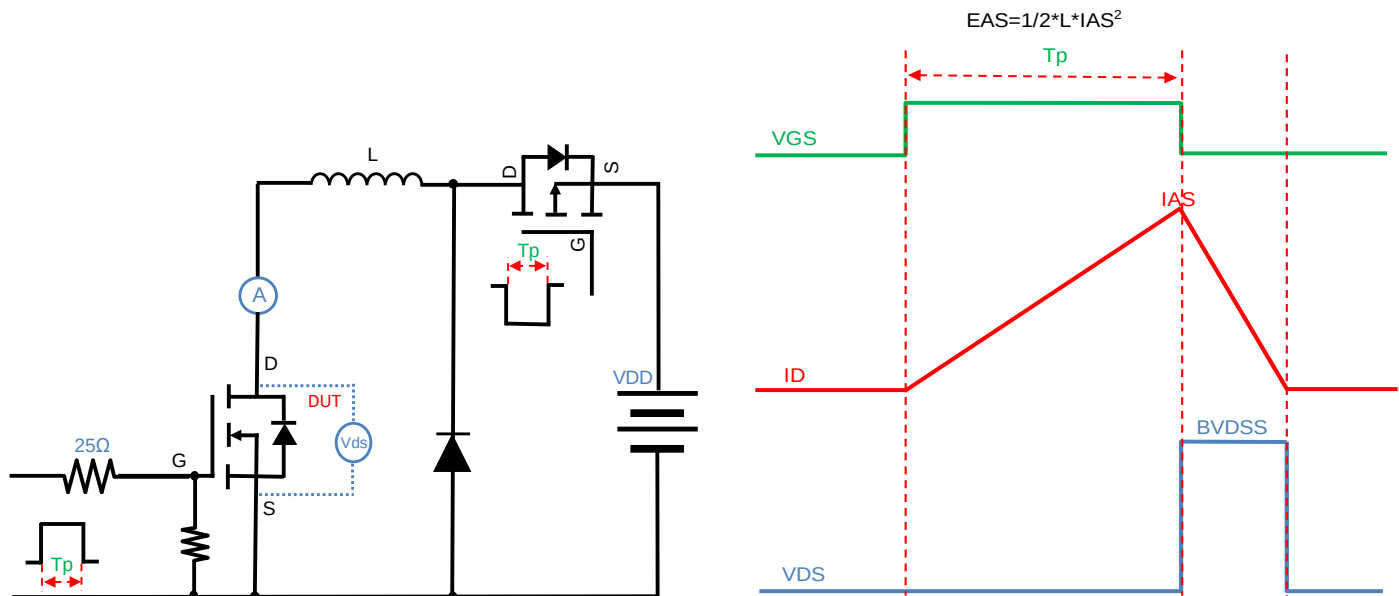


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

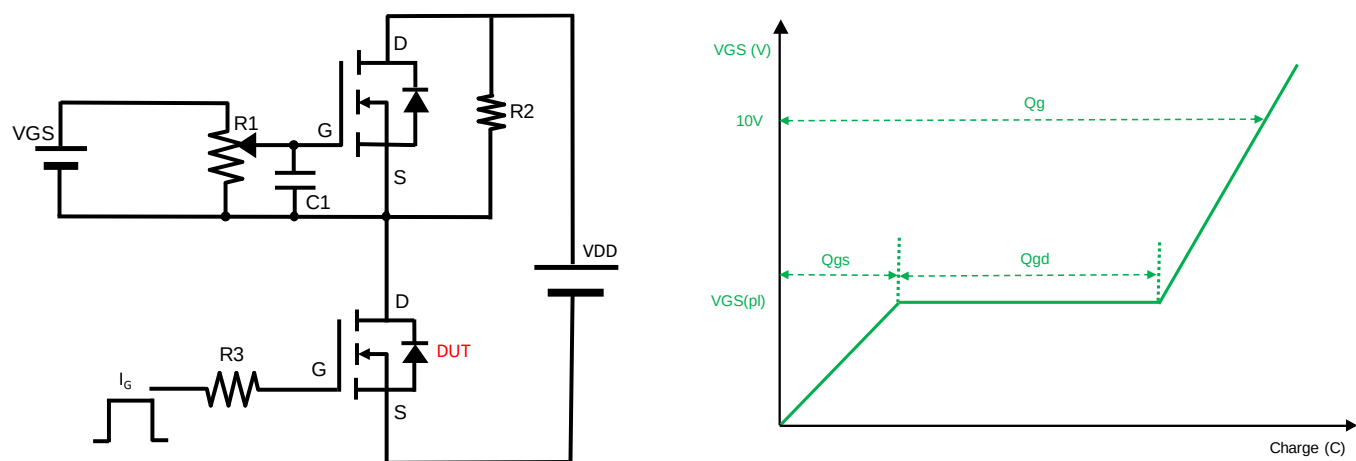


Figure B. Gate Charge Test Circuit & Waveform

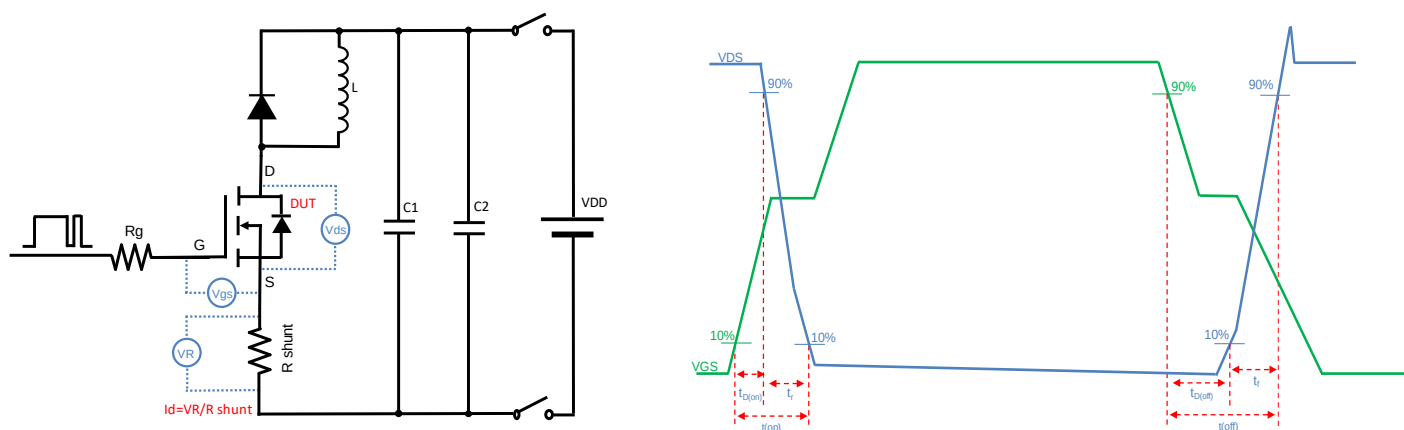


Figure C. Resistive Switching Test Circuit & Waveform

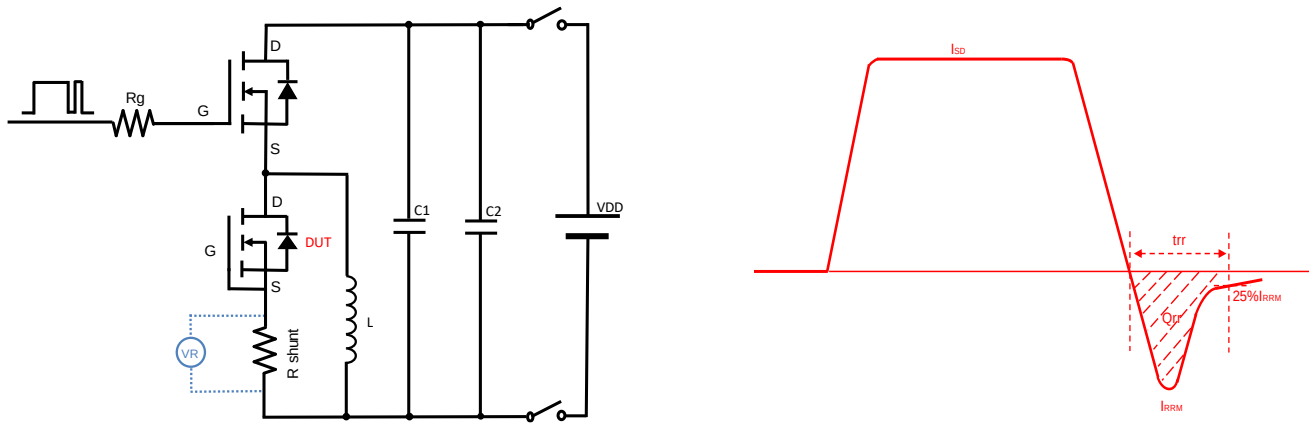
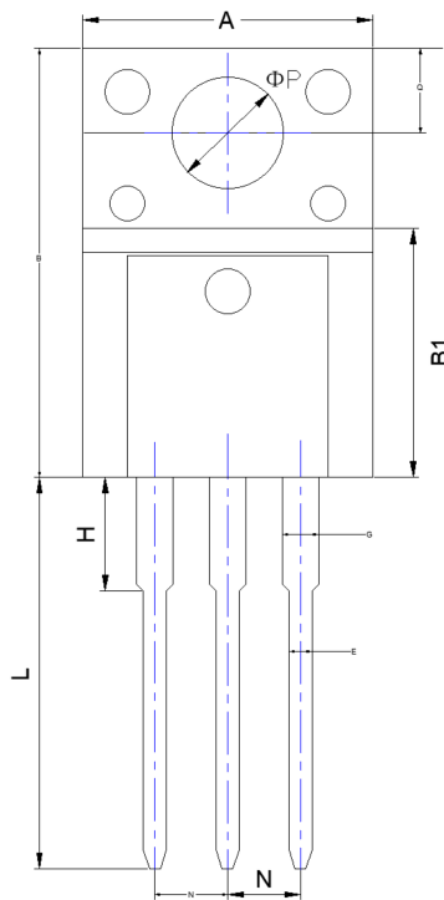


Figure D. Diode Recovery Test Circuit & Waveform

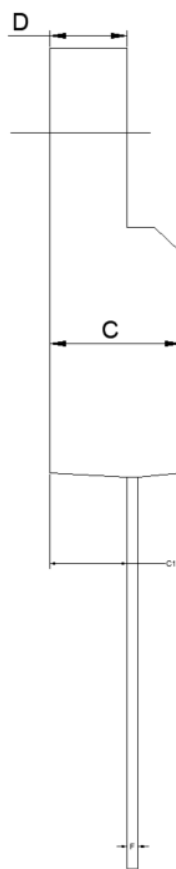


YJF1K0D65CHJ

■ ITO-220AB-F Package information



TOP VIEW



SIDE VIEW

SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.382	0.406	9.700	10.300
B	0.610	0.634	15.500	16.100
B1	0.354	0.374	8.990	9.490
C	0.177	0.193	4.500	4.900
C1	0.098	0.116	2.500	2.950
D	0.092	0.108	2.340	2.740
E	0.028	0.035	0.700	0.900
F	0.016	0.024	0.400	0.600
G	0.044	0.056	1.120	1.420
H	0.106	0.130	2.700	3.300
L	0.496	0.535	12.600	13.600
N	0.092	0.108	2.340	2.740
Q	0.124	0.140	3.150	3.550
ΦP	0.118	0.138	3.000	3.500

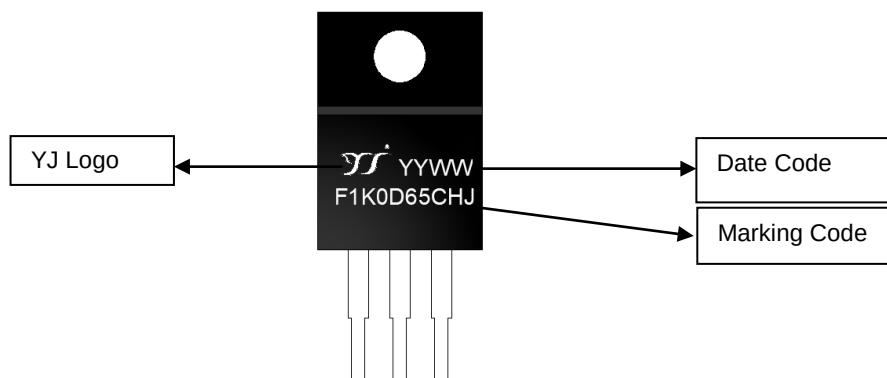
NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.



YJF1K0D65CHJ

■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. F1K0D65CHJ is marking code, YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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